

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ V _{GS} = 10V	360mA
	2.5Ω @ V _{GS} = 4.5V	250mA

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package
- ESD Protected to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under a separate datasheet ([DMN53D0LDWQ](#))**

Mechanical Data

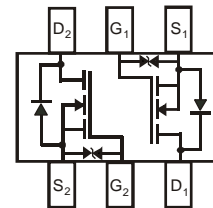
- Package: SOT363
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208③
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



SOT363 (Standard)



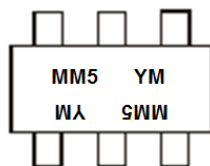
Top View


 Top View
 Internal Schematic

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN53D0LDW-7	SOT363 (Standard)	3000	Tape & Reel
DMN53D0LDW-13	SOT363 (Standard)	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


MM5 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: M = 2025)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2014	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	B	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	360	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	411	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	—	—	V	V _{GS} = 0, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 50V, V _{GS} = 0
Gate-Body Leakage	I _{GSS}	—	—	10	μA	V _{GS} = ±20V, V _{DS} = 0
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	—	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.0	1.6	Ω	V _{GS} = 10V, I _D = 500mA
		—	1.0	2.5		V _{GS} = 4.5V, I _D = 200mA
		—	1.4	4.5		V _{GS} = 2.5V, I _D = 100mA
Source-Drain Diode Forward Voltage	V _{SD}	—	0.8	1.4	V	V _{GS} = 0, I _S = 500mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	46	—	pF	V _{DS} = 25V, V _{GS} = 0, f = 1.0MHz
Output Capacitance	C _{oss}	—	5.3	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	4.0	—	pF	
Total Gate Charge	Q _g	—	0.6	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.7	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _R	—	2.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	19	—	ns	
Turn-Off Fall Time	t _F	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

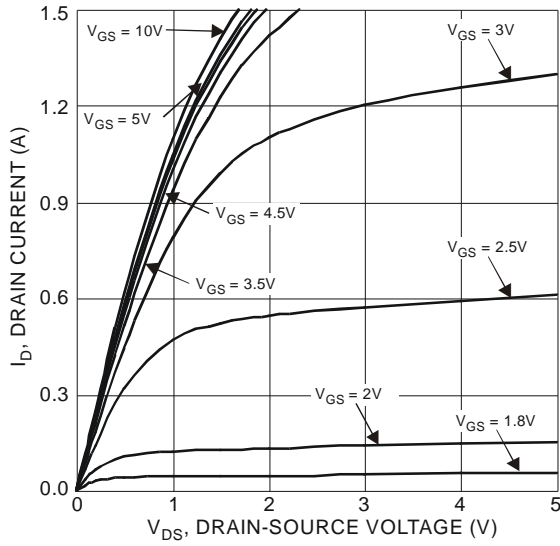


Figure 1 Typical Output Characteristics

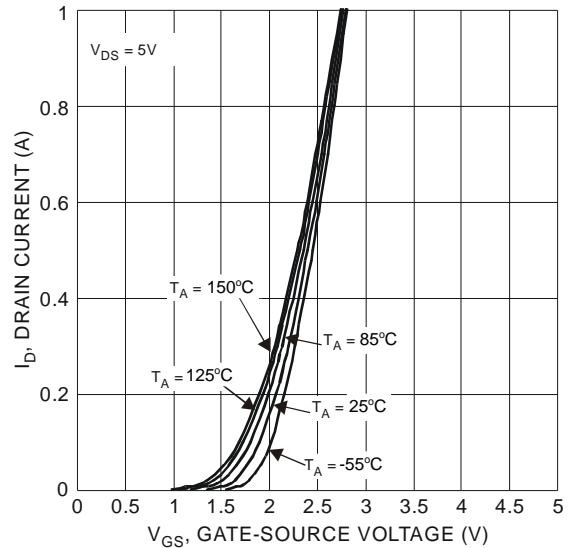


Figure 2 Typical Transfer Characteristics

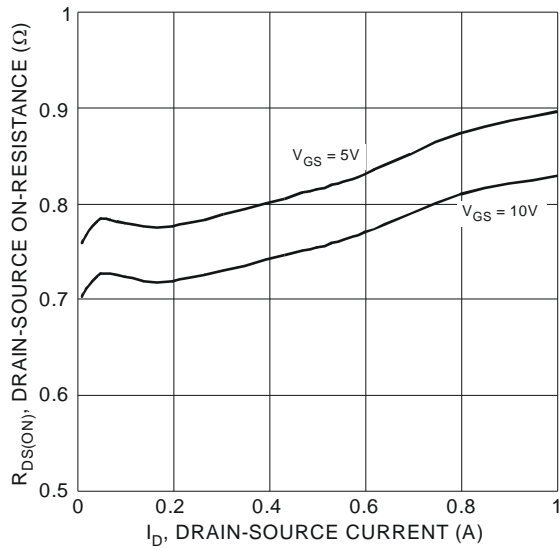


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

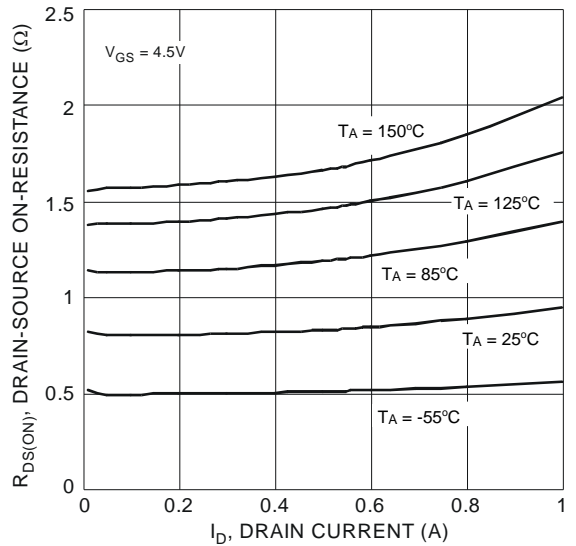


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

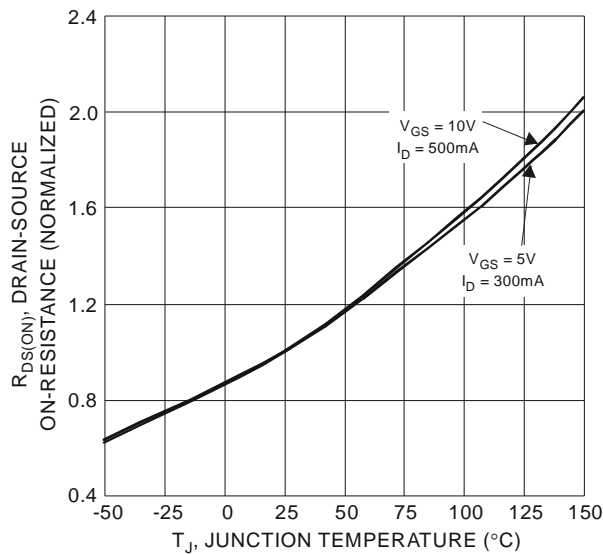


Figure 5 On-Resistance Variation with Temperature

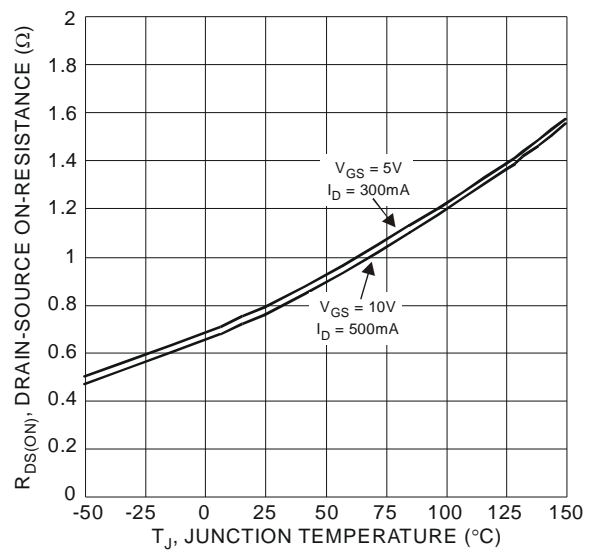


Figure 6 On-Resistance Variation with Temperature

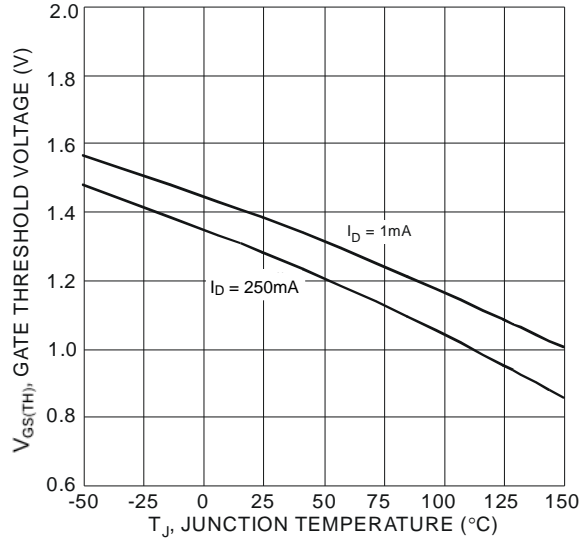


Figure 7 Gate Threshold Variation vs. Junction Temperature

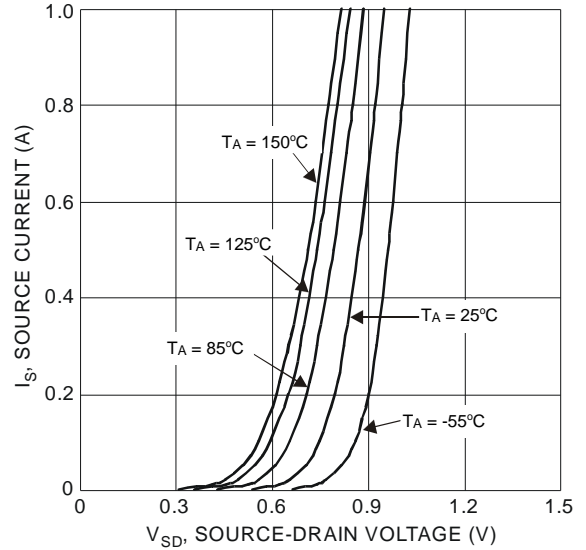


Figure 8 Diode Forward Voltage vs. Current

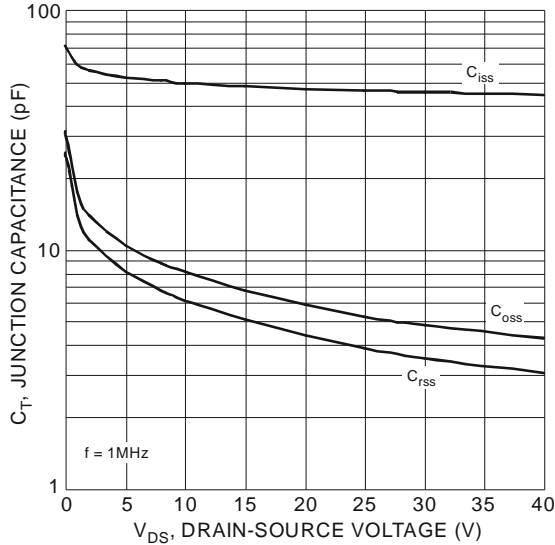


Figure 9 Typical Junction Capacitance

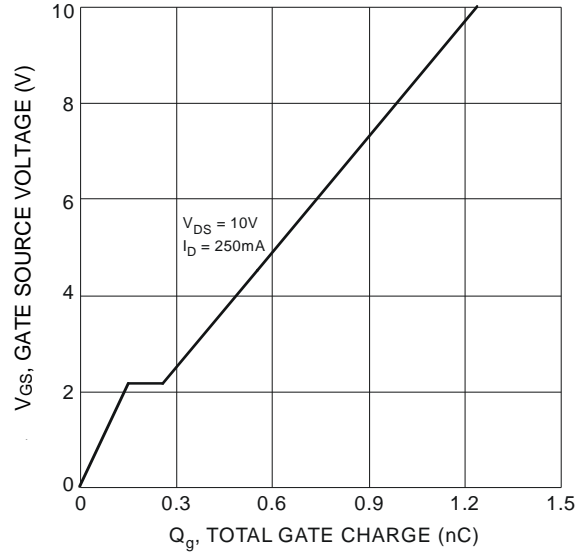
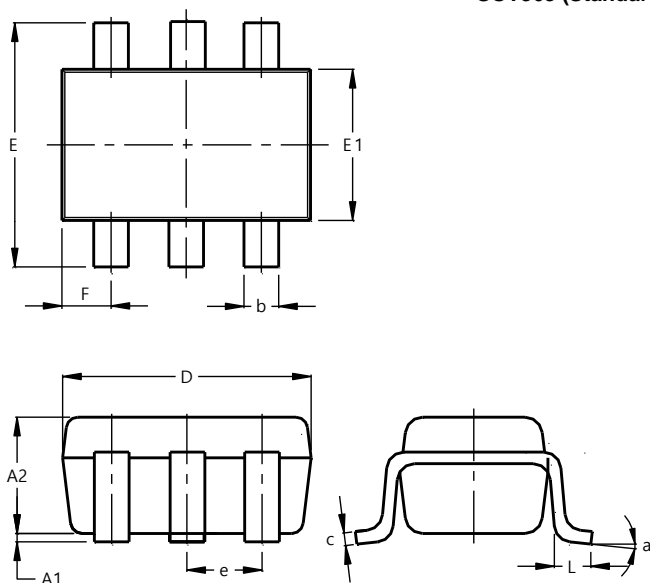


Figure 10 Gate Charge

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

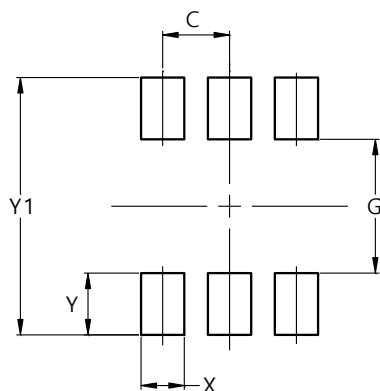


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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